

# RJJ0621DPP

# P Channel Power MOS FET High Speed Switching

REJ03G1624-0200 Rev.2.00 Jun 16, 2008

### **Features**

• V<sub>DSS</sub>: -60 V

•  $R_{DS(on)}$ : 56 m $\Omega$  (MAX)

•  $I_D: -25 A$ 

• Lead Mount Type (TO-220FN)

### **Outline**

RENESAS Package code: PRSS0003AB-A (Package name : TO-220FN)

1. Gate 2. Drain 3. Source

# **Application**

• DC-DC converter, Motor control, Solenoid control, etc.

# **Absolute Maximum Ratings**

 $(Tc = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit	Conditions
Drain to source voltage	$V_{DSS}$	-60	V	$V_{GS} = 0 V$
Gate to source voltage	$V_{GSS}$	+10/–20	V	$V_{DS} = 0 V$
Drain current (DC)	I <sub>D</sub>	-25	Α	
Drain current (Pulsed)*1	I <sub>D(pulse)</sub>	<b>-</b> 50	Α	
Avalanche current	I <sub>AP</sub>	-25	Α	L = 100 μH
Channel dissipation	P <sub>ch</sub>	35	W	
Channel to case thermal impedance	θch-c	3.57	°C/W	
Channel temperature	Tch	−55 to +150	°C	
Storage temperature	Tstg	-55 to +150	°C	

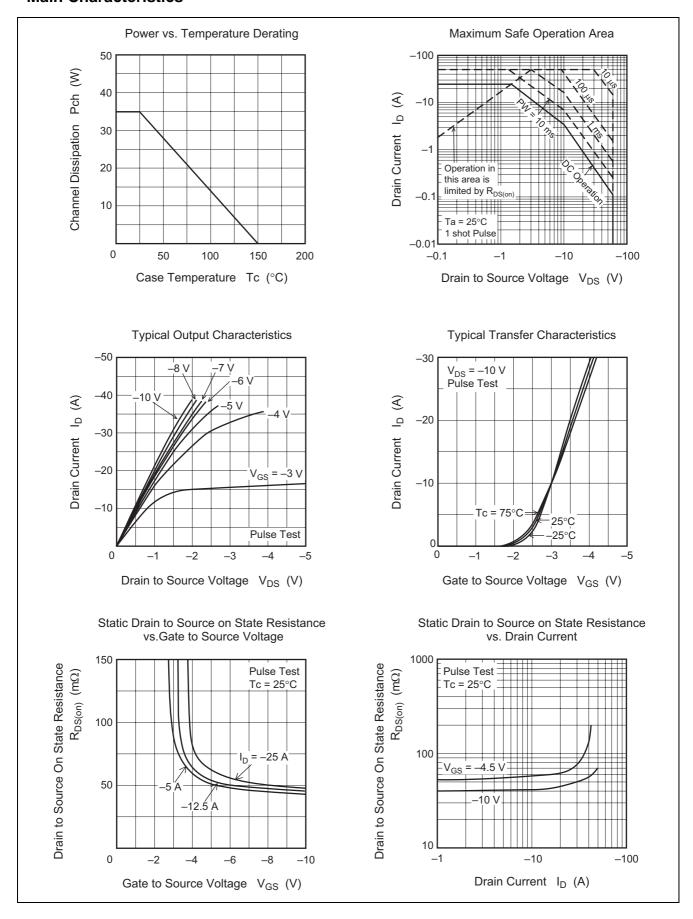
Note: 1. Pulse width limited by safe operating area.

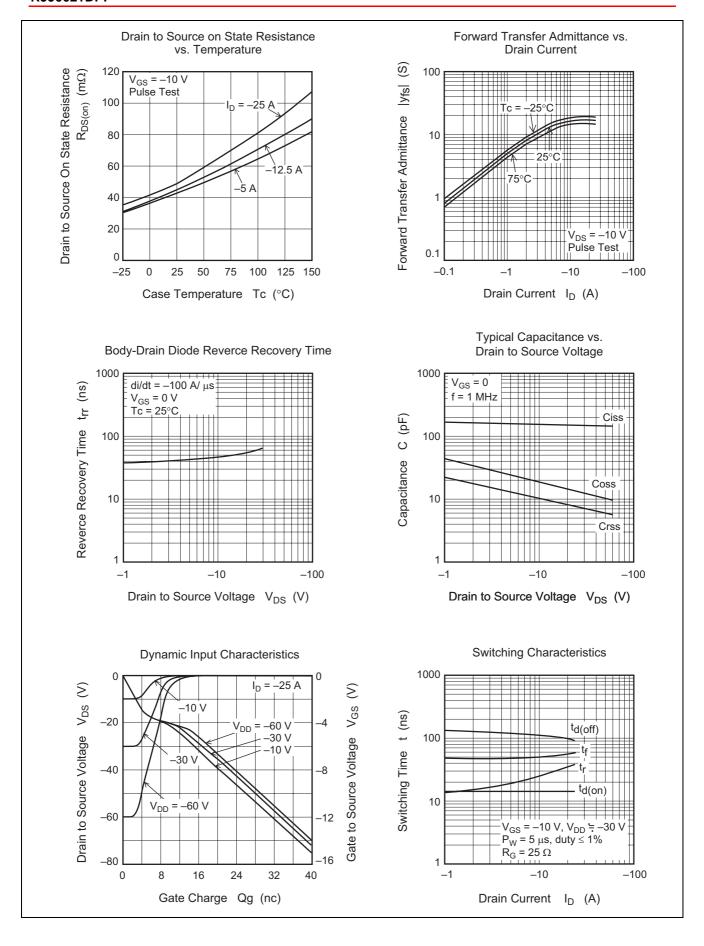
# **Electrical Characteristics**

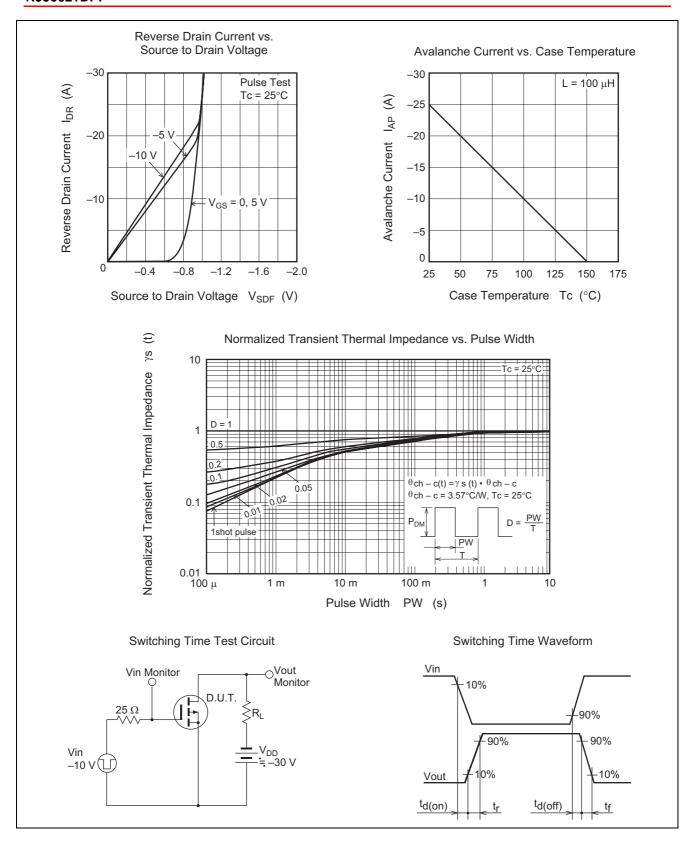
 $(Tc = 25^{\circ}C)$ 

Item	Symbol	Min.	Тур.	Max.	Unit	Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	_	_	V	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$
Drain to source leakage current	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$
Gate to source leak current	I <sub>GSS</sub>	_	_	0.1	μΑ	$V_{GS} = +10 \text{ V}, V_{DS} = 0 \text{ V}$
Gate to source leak current	I <sub>GSS</sub>	_	_	-0.1	μΑ	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	-1.0	-1.7	-2.5	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Static drain to source on state	R <sub>DS(on)</sub>	_	45	56	mΩ	$I_D = -12.5 \text{ A}, V_{GS} = -10 \text{ V}$
resistance		_	65	95	mΩ	$I_D = -12.5 \text{ A}, V_{GS} = -4.5 \text{ V}$
Input capacitance	Ciss	_	1550	_	pF	V <sub>DS</sub> = -10 V
Output capacitance	Coss	_	190	_	pF	$V_{GS} = 0 V$
Reverse transfer capacitance	Crss	_	100	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	15	_	ns	$V_{DD} = -30 \text{ V}$
Rise time	t <sub>r</sub>	_	25	_	ns	$I_D = -12.5 \text{ A}$
Turn-off delay time	t <sub>d(off)</sub>	_	100	_	ns	$V_{GS} = -10 \text{ V}$
Fall time	t <sub>f</sub>	_	50	_	ns	$R_G = 25 \Omega$
Body-drain diode forward voltage	$V_{DF}$	_	-0.9	-1.5	V	$I_F = -12.5 \text{ A}, V_{GS} = 0 \text{ V}$

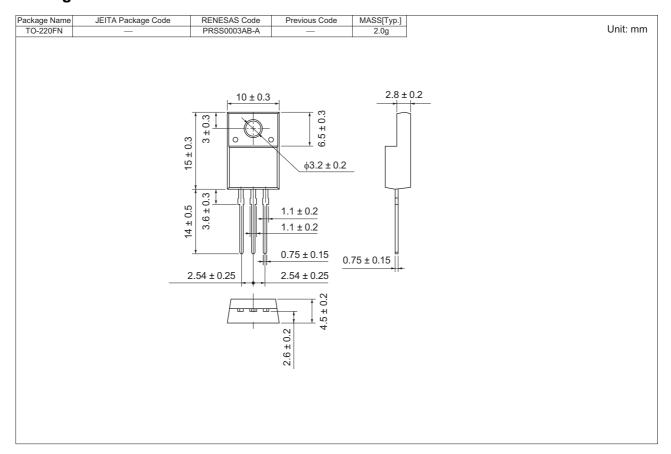
## **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJJ0621DPP-00-T2	50 pcs	Magazine (Tube)

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